

Low Voltage Standard Rectifier

Single Diode

$$V_{RRM} = 1200 \text{ V}$$

$$I_{FAV} = 60 \text{ A}$$

$$V_F = 1 \text{ V}$$

Part number

DLA 60 I 1200 HA



Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package:

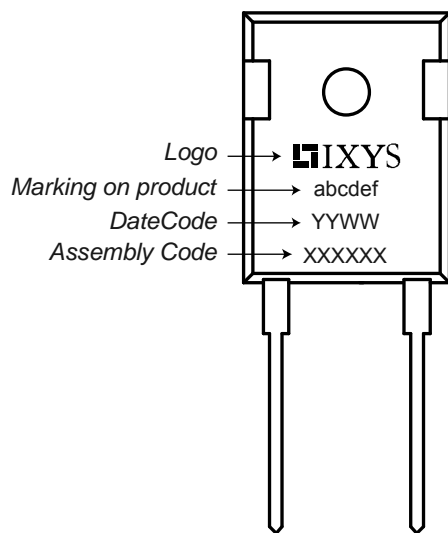
- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

Symbol	Definition	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage				1200	V	
I_R	reverse current	$V_R = 1200 \text{ V}$			20	μA	
		$V_R = 1200 \text{ V}$			0.1	mA	
V_F	forward voltage	$I_F = 60 \text{ A}$			1.10	V	
		$I_F = 120 \text{ A}$			1.26	V	
		$I_F = 60 \text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.00	V
		$I_F = 120 \text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.16	V
I_{FAV}	average forward current	rectangular $d = 0.5$	$T_C = 150^\circ\text{C}$		60	A	
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^\circ\text{C}$		0.80	V	
r_F	slope resistance				3	m Ω	
R_{thJC}	thermal resistance junction to case				0.30	K/W	
T_{VJ}	virtual junction temperature		-55		175	$^\circ\text{C}$	
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$	500	W	
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		850	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 \text{ V}$		920	A	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^\circ\text{C}$		725	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 \text{ V}$		780	A	
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		3.62	kA ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 \text{ V}$		3.52	kA ² s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^\circ\text{C}$		2.63	kA ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 \text{ V}$		2.53	kA ² s	
C_J	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		33	pF	

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per pin ¹⁾			70	A
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

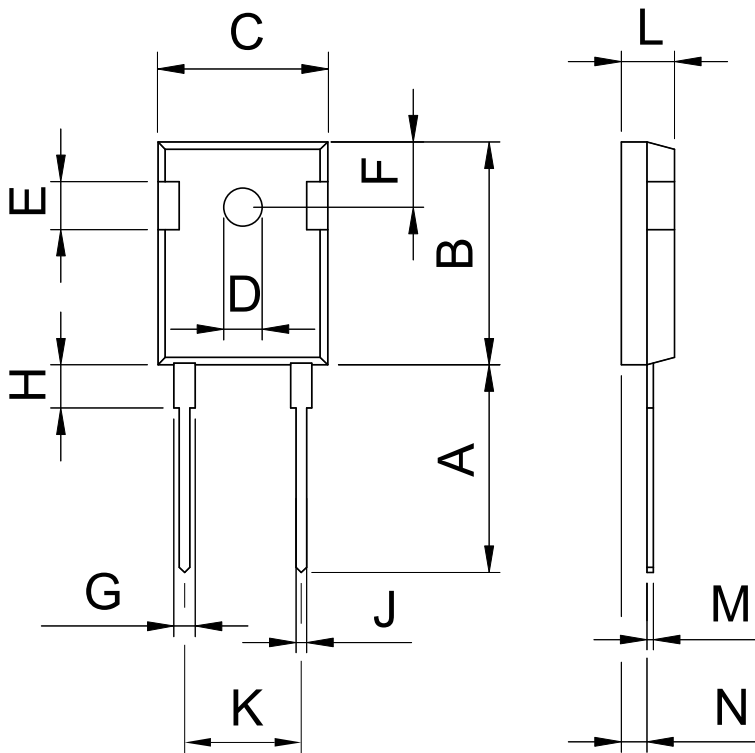
¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.
 In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Product Marking

Part number

D = Diode
 L = Low Voltage Standard Rectifier
 A = (up to 1200V)
 60 = Current Rating [A]
 I = Single Diode
 1200 = Reverse Voltage [V]
 HA = TO-247AD (2)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DLA 60 I 1200 HA	DLA60I1200HA	Tube	30	508170

Outlines TO-247



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102